

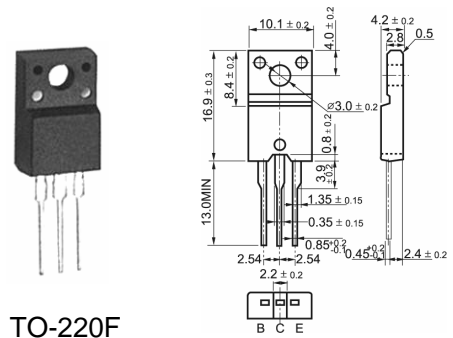


BUT11AF

SILICON DIFFUSED POWER TRANSISTOR

GENERAL DESCRIPTION

Highvoltage,high-speed switching npn transistors in a metal envelope ,primarily for use in switching power circuits.



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0V$		1000	V
V_{CEO}	Collector-emitter voltage (open base)			450	V
I_C	Collector current (DC)			5	A
I_{CM}	Collector current peak value			10	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25^\circ C$		40	W
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 2.5A; I_B = 0.5A$		1.5	V
I_{csat}	Collector saturation current	$f = 16KHz$			A
V_F	Diode forward voltage				V
t_f	Fall time	$I_C=2.5A, I_{B1}=-I_{B2}=0.5A, V_{CC}=150V$		1.0	μs

LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0V$		1000	V
V_{CEO}	Collector-emitter voltage (open base)			450	V
V_{EBO}	Emitter-base voltage(open collector)			5	V
I_C	Collector current (DC)			5	A
I_B	Base current (DC)			2	A
I_{BM}	Base current peak value			4	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25^\circ C$		40	W
T_{stn}	Storage temperature		-55	150	$^\circ C$
T_j	Junction temperature			150	$^\circ C$

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{CE}	Collector-emitter cut-off current	$V_{BE} = 0V; V_{CE} = V_{CESMmax}$		1.0	mA
I_{CES}		$V_{BE} = 0V; V_{CE} = V_{CESMmax}$		2.0	mA
$V_{CEO sust}$	Collector-emitter sustaining voltage	$T_j = 125^\circ C$ $I_B = 0A; I_C = 100mA$ $L = 25mH$			V
V_{CEsat}	Collector-emitter saturation voltages	$I_C = 2.5A; I_B = 0.5A$		1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = 2.5A; I_B = 0.5A$		1.5	V
h_{FE}	DC current gain	$I_C = 0.5A; V_{CE} = 5V$	10	50	
V_F	Diode forward voltage				V
f_T	Transition frequency at $f = 1MHz$	$I_C = 0.1A; V_{CE} = 10V$	5		MHz
C_c	Collector capacitance at $f = 1MHz$	$V_{CB} = 10V$			pF
t_s	Switching times(16KHz line deflecton circuit)	$I_C=2.5A, I_{B1}=-I_{B2}=0.5A, V_{CC}=150V$		5.0	μs
t_f	Turn-off storage time Turn-off fall time	$I_C=2.5A, I_{B1}=-I_{B2}=0.5A, V_{CC}=150V$		1.0	μs